

# Preliminary estimate of the noise achievable in a FCC-ee/LAr calorimeter

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## 1) Estimation of the sampling fraction in “baseline” and some variant

Dedx plomb=12,7 MeV/cm	X0 Pb= 0.56 cm
Fer = 11,4 MeV/cm	X0 Fe= 1.76 cm
Dedx Lar = 2,13 MeV/cm	X0 LAr= 14 cm
Dedx G10 = 3,1 MeV/cm*	X0G10= 17 cm

\*my own estimate from 60% glass, 40% “polycarbonate” as a proxy to epoxy  
3.17 from private/Martin

### 1.1) Baseline design/ Martin:

absorber = 1.4mmPb + 2x0.2mm Fe + 2x0.1mm G10= 2mm

Electrode = 1.2mm G10

A radial track crosses 42 absorbers with an average angle of 45 degrees (goes from 50 to 40 )

Lead 1.4mm\*42\*1.41= 83 mm Pb -> 14.8 X0 and 105 MeV dEdx

G10 1.4mm\*42\*1.41=83 mmG10 -> 0.5 X0 and 26 MeV

Fe 0.4mm\*42\*1.41=24 mm Fe -> 1.4 X0 and 27 MeV

Argon (comp. to 400mm) =210 mm Ar-> 1.5 X0 and 44 MeV →

**Total 18.2 X0 and 202 MeV**

Sampling Fraction Lar= 44/202= 21.8% (average: SF increases from front to back)

Average track length in a double gap= 210/42= 5mm (gap is narrower by  $\sqrt{2}$ )

### 1.2) With 2 steps of + 0.6 mm lead ie absorbers of 2mm, then 2.6, then 3.2mm thickness

Lead is increased by 14\*0.6\*1.4 + 14\*1.2\*1.4= 35 mm

LAr is decreased by the same amount:

For the same radial track:

Lead 2mm\*42\*1.41= 118 mm Pb -> 21 X0 and 149 MeV dEdx

G10 1.4mm\*42\*1.41=83 mmG10 -> 0.5 X0 and 26 MeV

Fe 0.4mm\*42\*1.41=24 mm Fe -> 1.4 X0 and 27 MeV

Argon 175 mmAr-> 1.2 X0 and 37 MeV

**Total 24.1 X0 and 239 MeV**

Sampling Fraction Lar= 37/239 = 15.5 %

Average track length in a double gap =  $175/42 = 4.2\text{mm}$  (dble gap is narrower by  $\sqrt{2}$ )  
 → probably not a good solution; too thick in terms of X0.  
 Could allow a “shorter” calorimeter if dictated by other constraints

- 1.3) Thinner absorbers at the beginning, then 2 steps of + 0.6 mm lead ie  
 absorbers of 0.6mm for PS, then 1.6mm, then 2.2 mm, then 2.8mm thickness  
 Lead thickness is 0mm for PS, then 1mm, then 1.6mm, then 2.2mm

For the same radial track:

Lead	$1.6\text{ mm} * 42 * 1.41 = 95\text{ mm Pb}$	->	17 X0 and 121MeV dEdx
G10	$1.4\text{mm} * 42 * 1.41 = 83\text{ mmG10}$	->	0.5 X0 and 26 MeV
Fe	$0.4\text{mm} * 42 * 1.41 = 24\text{ mm Fe}$	->	1.4 X0 and 27 MeV
Argon	198 mmAr	->	1.4 X0 and 42 MeV

**Total** **20.3 X0 and 216 MeV**

Sampling Fraction LAr =  $42/216 = 19.4\%$

Average track length in a double gap =  $198/42 = 4.7\text{mm}$  ( $/\sqrt{2} \rightarrow \text{dble gap} = 3.4\text{ mm}$ )

For consistency with the depth segmentation, the split into 3 parts (+presampler) could take place:

After pad 1 and 2 absorbers for the presampler part	gap= 1.72 to 1.76mm
pad 5 and 18 absorbers for the first part, Pb =1mm t=220mm	gap= 1.46 to 1.87mm
pad 8 and 30 absorbers for the 2 <sup>nd</sup> part, Pb =1.6mm t=385mm	gap= 1.57 to 1.91
pad11 and 42 absorbers for the last part, Pb =2.6mm t=568mm	gap= 1.61 to 1.98

The number of X0 for each segment is thus 6.8 X0 for the first one (PS included), 5.8 for the second and 7.6 for the third one (at  $\theta=90$  degrees).

All gaps being between 1.5 and 2 mm, a constant high voltage could perhaps accommodate them.

The sampling fraction in the 3 segments is correspondingly about:25%,19% and 15%. The signals from the first 4 pads (the last 3) would have to be scaled down by a factor 0.76 (up by a factor 1.27) in a first approximation.

## 2) From deposited energy to Collected charge.

Take 19% as sampling fraction and 90% charge survival (recombination...)

Take 26 eV as the average energy loss per electron-ion pair created (debatable, perhaps a smaller value around 24 eV is better...)

**Collected charge for 1 MeV deposited =  $10^6\text{ eV} / (2 * 26)\text{ eV} * 0.17 = 3200\text{ electrons}$**

(factor 2 because positive ions are not collected during the integration time)

### 3) Noise Estimate

In the charge collection mode, the dominant series noise  $Q(\text{rms})$  is proportional to the capacitance at input, inversely proportional to  $g_m$  of the input transistor and to the peaking time  $\tau_P$ .

$$Q = C \times \sqrt{4kT / (g_m \times \tau_P)}$$

#### 2.1 Noise at Dune

**Cold PA from BNL :**

-spec noise rms = 1000 electrons for 200 pF capacitance, and 1  $\mu\text{s}$  integration time.

**PA directly connected to sensor (wire) no cables,...**

MOSfet PA 180nm; performance improves at cold (factor  $\sim 2$ )

1/f noise under control for shaping time not longer than  $\sim$  a few  $\mu\text{s}$

Power dissipation: 5mW PA alone, 50 mW for full chain

-measurements : somewhat better than spec

-Reference: G. De Geronimo et al., Front-end ASIC for a liquid argon TPC, [IEEE Transactions on Nuclear Science 58 \(2011\) 1376–1385](#).

Cold PA from Lyon, for Dune as well -> similar performance (no published reference found)

#### 2.2 Noise per cell at FCC ee

Capacitance ; not yet fully settled depends on geometry

Brieuc Francois reports  $200 < C < 1000 \text{pF}$

Takes these 2 extremes :

Assuming noise as in the specs of Dune:

- 200 pF -> 1000 electrons  $\leftrightarrow$  0.3 MeV

- 500 pF -> 2500 electrons  $\leftrightarrow$  0.8 MeV

-1000pF-> 5000 electrons  $\leftrightarrow$  1.5 MeV

=> take 1 MeV as “ average ” until capacitances are known better

#### 2.3 Noise per “ cluster ” at FCC ee

Assumes “coherent” noise remains incoherent even for hundreds of cells together (a general problem for highly granular calorimeters).

-for muons: 2 cells in rphi, 1 or 2 in theta, 12 in depth  $\rightarrow$   $\leq 48$  cells ie 7 MeV for a  $\sim 200 \text{MeV}$  signal ; in average  $\sim 5 \text{MeV}$  signal per cell ; S/N  $\sim 5$  per cell

-for high energy EM shower :  $3 \times 3 \times 12 \rightarrow \sim 100$  cells -> 10 MeV

-for low energy EM shower :  $3 \times 2 \times 8 \rightarrow 50$  cells  $\rightarrow 7 \text{MeV}$

At 1 GeV ,  $5\%/\sqrt{E}$  -> 50 MeV sampling fluctuation-> electronics noise remains comparatively small

➔ **Cold preamps “ a la Dune” would give superb noise performance**

Possible problem: dynamic range. For Dune it is limited to about 2000.  
at FCC-ee a very rough estimate of the maximum deposited energy per cell is  $\sim 10$  GeV,  
meaning a dynamical range of 10 000 , or 14 bits. Coping with this is likely to require more power dissipation....